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¹Dept. of Electrical and Computer Engineering, Auburn University, Auburn, AL 36849; ²Dept. of Physics, Auburn University, Auburn, AL 36849
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¹Department of Electrical Engineering, University of Notre Dame, Notre Dame, IN 46556, USA; ²ECE Department and Birck Nanotechnology Center, Purdue University, West Lafayette, IN 47907, USA
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3:10 PM Yi Song¹, Parsian K. Mohseni¹, Seung Hyun Kim¹, Jae Cheol Shin², Chen Zhang¹, Kelson Chabak^{1,3} and Xiuling Li^{1*}, ¹Department of Electrical and Computer Engineering, University of Illinois at Urbana-Champaign, Urbana, IL 61801 USA; ²Department of physics, Yeungnam University, Republic of Korea; ³Air Force Research Laboratory, Sensors Directorate, Wright-Patterson AFB, OH 45433 USA
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3:50 PM Cezar B. Zota, Lars-Erik Wernersson and Erik Lind Department of Electrical and Information Technology, Lund University, Sweden
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4:10 PM M. Barth¹, G. B. Rayner Jr.², S. Mack³, B.R. Bennett³, and S. Datta¹ ¹The Pennsylvania State University, University Park, PA 16802, USA; ²Kurt J. Lesker Company, Pittsburgh, PA 15025, USA; ³Naval Research Laboratory, Washington, DC 20375 USA
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- R.2 **Device Modeling: Do we need any new models? &* %**
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Shuji Nakamura; Materials and ECE Departments, University of California Santa Barbara, Santa Barbara, California, USA

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11:00 AM Deepika Yadav¹, Stephane Boubanga Tombet¹, Takayuki Watanabe¹, Victor Ryzhii^{1,2}, and Taiichi Otsuji¹
¹Research Institute of Electrical Communication, Tohoku University, Sendai 980-8577, Japan; ²Institute of Ultra-High-Frequency Semiconductor Electronics, RAS, Moscow 111005, Russia
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10:00 AM Heng Wu, Nathan Conrad, Mengwei Si, and Peide D. Ye* School of Electrical and Computer Engineering, Purdue University, West Lafayette, IN 47906, USA
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10:20 AM Nidhi Agrawal¹, Ashish Agrawal¹, Subhadeep Mukhopadhyay², Souvik Mahapatra², and Suman Datta¹
¹The Pennsylvania State University, University Park, USA; ²Indian Institute of Technology Bombay, Mumbai, India
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10:40 AM Shraddha Kothari, Chandan Joishi, Dipankar Biswas, Dharendra Vaidya, Swaroop Ganguly and Saurabh Lodha Dept. of Electrical Engineering, IIT Bombay, Powai, Mumbai, India- 400076
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11:00 AM Pragya Kushwaha¹, Harshit Agarwal¹, Sourabh Khandelwal², Juan-Pablo Duarte², Aditya Medury², Chenming Hu², and Yogesh S. Chauhan¹ ¹Nanolab, Department of Electrical Engineering, Indian Institute of Technology Kanpur, India; ²Electrical Engineering and Computer Science, University of California Berkeley, USA
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¹Institute of Semiconductor Engineering, University of Stuttgart, Stuttgart, Germany; ²Dept. of Electrical Engineering, IIT Bombay, Mumbai, India
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11:40 AM J. Kwon¹, A. A. Sharma², J. A. Bain², Y. N. Picard¹, and M. Skowronski¹ ¹Materials Science and Engineering Department, ²Electrical and Computer Engineering Department, Carnegie Mellon University, 5000 Forbes Ave., Pittsburgh, PA 15213, USA